

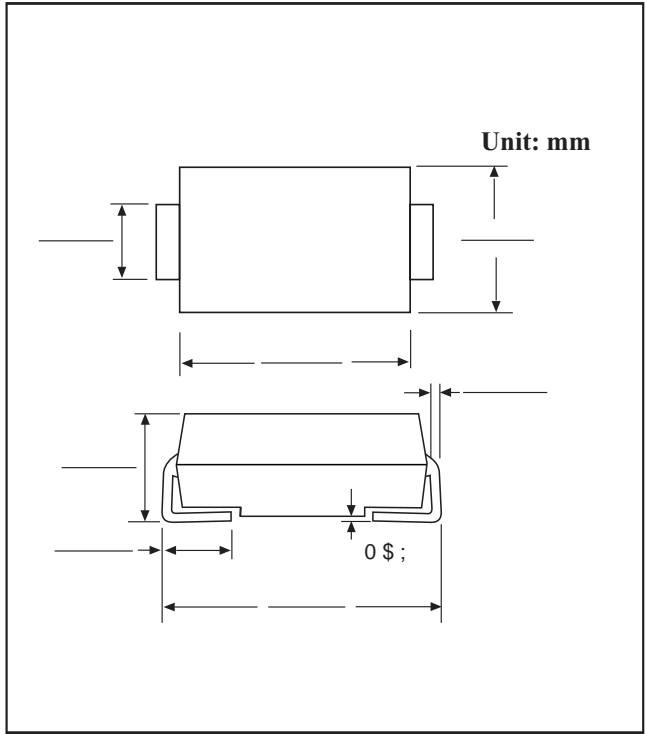
SM % PLASTIC SILICON RECTIFIERS

FEATURES

- "Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing
- "Metal silicon junction ,majoritycarrier conduction
- "Built-in strain relief
- "For surfacemounted applications
- "Low power loss ,high efficiency,High surge capability
- "High current capability ,Low forward voltage drop
- "For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- "High temperature soldering guaranteed:260 °C/10 seconds at terminals
- "Component in accordanceto RoHS and WEEE

(8) MECHANICAL DATA

- "Case:SM % moldedplasticbody
- "Terminals:Lead solderable per MIL-STD-750,method 2026
- "Polarity:Color band denotes cathode end



MAXIMUM RATINGS AND CHARACTERISTICS

f & \$ P E L H 7 G W S H U D X X Q U R H W K H Q Z L W H G

TYPE NUMBER	SYMBOL	SS 2	S 6	SS 4	SS 5	SS 6	SS 8	SS 1	UNITS
Maximum recurrent peak reverse voltage	V _{RRM}	20	30	40	50	60	80	1 0	V
Maximum RMS voltage	V _{RMS}	14	21	28				7	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	1	V
Maximum Average Forward rectified Current 0.375"(9.5mm) lead length	I _{F(AV)}							.0	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I _{FSM}							0.0	A
Maximum instantaneous forward voltage at .0 A(Note1)	V _F		0.		0.		0.		V
Maximum reverse current at rated DC blocking voltage per diode	@T _A =25								mA
	@T _A =100			0.0			10.0		
7 \ S L F D O 7 K H U P D O 5 H V L V W D Q F H 1 R W H	R _{θJA}								/W
€ f z r) € t z € t r f r t z € t v q , v D	T _I		00						S)
Storage Temperature	T _{STG}							- ---- + 150	
Operation Junction Temperature	T _J			- 5 ---- + 125				- ---- + 150	

Notes: B a ^ t v t v K D A A I I I I f ^ t v S z t y = B 6 u ^ t t e v C . k T S 2 - , ^ e v u I A F F j N . f ^ 4 I f r u & 4 v t C . v & t 5 v u & u B k e u 1 5 v ^ 4 t v t , k t v 1 u Q